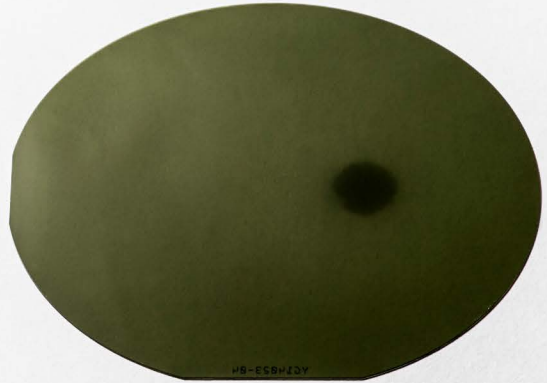


SiC wafer



Future power device material, Realize ultimate surface roughness and TTV in short time with low cost

We unique polishing technology of SiC wafers

We and IMRAM (institute of multidisciplinary Research for advanced materials) Tohoku university have been developing an innovative technology for SiC (silicon carbide) wafers.

Why We developed SiC polishing technology?

SiC is an outstanding material for next generation power devices, but for its stableness and hardness, the process cost is non-negligible problem. Therefore we started joint development of polishing technology for SiC wafer with IMRAM, Tohoku univ and AIST. We have been achieving superior quality (roughness and TTV) with short process time and low-cost.

Specification of SiC wafer

For more information, please contact us.

- From one piece to large scale production
- From material procurement to all processing processes
- For more information on delivery time, price and other specifications, please contact us as follows